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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	21000
Number of Logic Elements/Cells	84000
Total RAM Bits	3833856
Number of I/O	118
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	285-LFBGA, CSPBGA
Supplier Device Package	285-CSFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5um5g-85f-8mg285i

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Acronyms in This Document

A list of acronyms used in this document.

Acronym	Definition
ALU	Arithmetic Logic Unit
BGA	Ball Grid Array
CDR	Clock and Data Recovery
CRC	Cycle Redundancy Code
DCC	Dynamic Clock Control
DCS	Dynamic Clock Select
DDR	Double Data Rate
DLL	Delay-Locked Loops
DSP	Digital Signal Processing
EBR	Embedded Block RAM
ECLK	Edge Clock
FFT	Fast Fourier Transforms
FIFO	First In First Out
FIR	Finite Impulse Response
LVCMOS	Low-Voltage Complementary Metal Oxide Semiconductor
LVDS	Low-Voltage Differential Signaling
LVPECL	Low Voltage Positive Emitter Coupled Logic
LVTTTL	Low Voltage Transistor-Transistor Logic
LUT	Look Up Table
MLVDS	Multipoint Low-Voltage Differential Signaling
PCI	Peripheral Component Interconnect
PCS	Physical Coding Sublayer
PCLK	Primary Clock
PDPR	Pseudo Dual Port RAM
PFU	Programmable Functional Unit
PIC	Programmable I/O Cells
PLL	Phase-Locked Loops
POR	Power On Reset
SCI	SERDES Client Interface
SERDES	Serializer/Deserializer
SEU	Single Event Upset
SLVS	Scalable Low-Voltage Signaling
SPI	Serial Peripheral Interface
SPR	Single Port RAM
SRAM	Static Random-Access Memory
TAP	Test Access Port
TDM	Time Division Multiplexing

2.2.2. Modes of Operation

Slices 0-2 have up to four potential modes of operation: Logic, Ripple, RAM and ROM. Slice 3 is not needed for RAM mode, it can be used in Logic, Ripple, or ROM modes.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note that LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed in one PFU using each LUT block in Slice 0 and Slice 1 as a 16 x 2-bit memory in each slice. Slice 2 is used to provide memory address and control signals.

A 16 x 2-bit pseudo dual port RAM (PDPR) memory is created in one PFU by using one Slice as the read-write port and the other companion slice as the read-only port. The slice with the read-write port updates the SRAM data contents in both slices at the same write cycle.

ECP5/ECP5-5G devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. [Table 2.3](#) lists the number of slices required to implement different distributed RAM primitives. For more information about using RAM in ECP5/ECP5-5G devices, refer to [ECP5 and ECP5-5G Memory Usage Guide \(TN1264\)](#).

Table 2.3. Number of Slices Required to Implement Distributed RAM

	SPR 16 X 4	PDPR 16 X 4
Number of slices	3	6

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information, refer to [ECP5 and ECP5-5G Memory Usage Guide \(TN1264\)](#).

Table 2.4 provides a description of the signals in the PLL blocks.

Table 2.4. PLL Blocks Signal Descriptions

Signal	Type	Description
CLKI	Input	Clock Input to PLL from external pin or routing
CLKI2	Input	Muxed clock input to PLL
SEL	Input	Input Clock select, selecting from CLKI and CLKI2 inputs
CLKFB	Input	PLL Feedback Clock
PHASESEL[1:0]	Input	Select which output to be adjusted on Phase by PHASEDIR, PHASESTEP, PHASELOADREG
PHASEDIR	Input	Dynamic Phase adjustment direction.
PHASESTEP	Input	Dynamic Phase adjustment step.
PHASELOADREG	Input	Load dynamic phase adjustment values into PLL.
CLKOP	Output	Primary PLL output clock (with phase shift adjustment)
CLKOS	Output	Secondary PLL output clock (with phase shift adjust)
CLKOS2	Output	Secondary PLL output clock2 (with phase shift adjust)
CLKOS3	Output	Secondary PLL output clock3 (with phase shift adjust)
LOCK	Output	PLL LOCK to CLKI, Asynchronous signal. Active high indicates PLL lock
STDBY	Input	Standby signal to power down the PLL
RST	Input	Resets the PLL
ENCLKOP	Input	Enable PLL output CLKOP
ENCLKOS	Input	Enable PLL output CLKOS
ENCLKOS2	Input	Enable PLL output CLKOS2
ENCLKOS3	Input	Enable PLL output CLKOS3

For more details on the PLL you can refer to the [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#).

2.5. Clock Distribution Network

There are two main clock distribution networks for any member of the ECP5/ECP5-5G product family, namely Primary Clock (PCLK) and Edge Clock (ECLK). These clock networks have the clock sources come from many different sources, such as Clock Pins, PLL outputs, DLLDEL outputs, Clock divider outputs, SERDES/PCS clocks and some on chip generated clock signal. There are clock dividers (CLKDIV) blocks to provide the slower clock from these clock sources. ECP5/ECP5-5G also supports glitchless dynamic enable function (DCC) for the PCLK Clock to save dynamic power. There are also some logics to allow dynamic glitchless selection between two clocks for the PCLK network (DCS).

Overview of Clocking Network is shown in [Figure 2.6](#) on page 20 for LFE5UM/LFE5UM5G-85 device.

2.5.1.2. Dynamic Clock Select

The Dynamic Clock Select (DCS) is a smart multiplexer function available in the primary clock routing. It switches between two independent input clock sources. Depending on the operation modes, it switches between two (2) independent input clock sources either with or without any glitches. This is achieved regardless of when the select signal is toggled. Both input clocks must be running to achieve functioning glitch-less DCS output clock, but it is not required running clocks when used as non-glitch-less normal clock multiplexer.

There are two DCS blocks per device that are fed to all quadrants. The inputs to the DCS block come from all the output of MIDMUXs and Clock from CIB located at the center of the PLC array core. The output of the DCS is connected to one of the inputs of Primary Clock Center MUX.

Figure 2.7 shows the timing waveforms of the default DCS operating mode. The DCS block can be programmed to other modes. For more information about the DCS, refer to [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#).

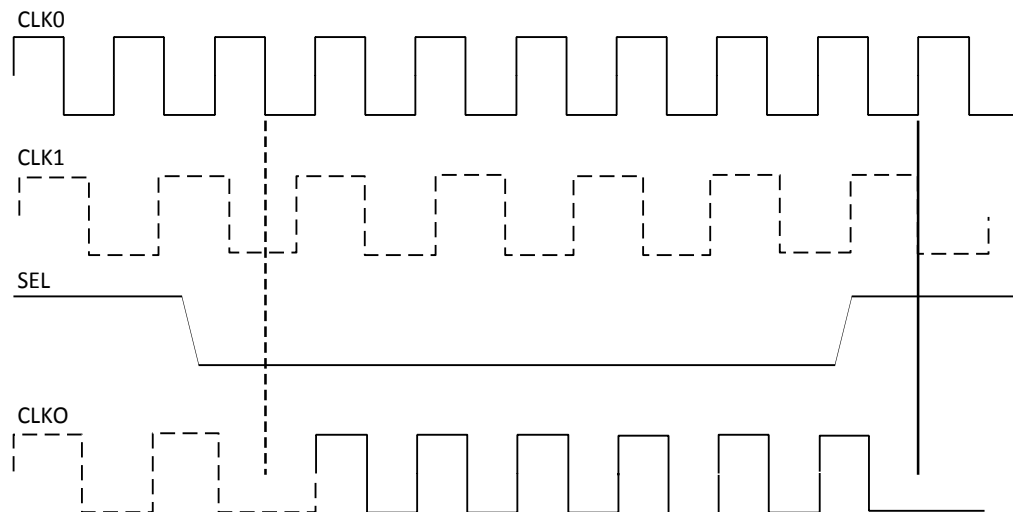


Figure 2.7. DCS Waveforms

2.5.2. Edge Clock

ECP5/ECP5-5G devices have a number of high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. There are two ECLK networks per bank IO on the Left and Right sides of the devices.

Each Edge Clock can be sourced from the following:

- Dedicated Clock input pins (PCLK)
- DLLDEL output (Clock delayed by 90°)
- PLL outputs (CLKOP and CLKOS)
- ECLKBRIDGE
- Internal Nodes

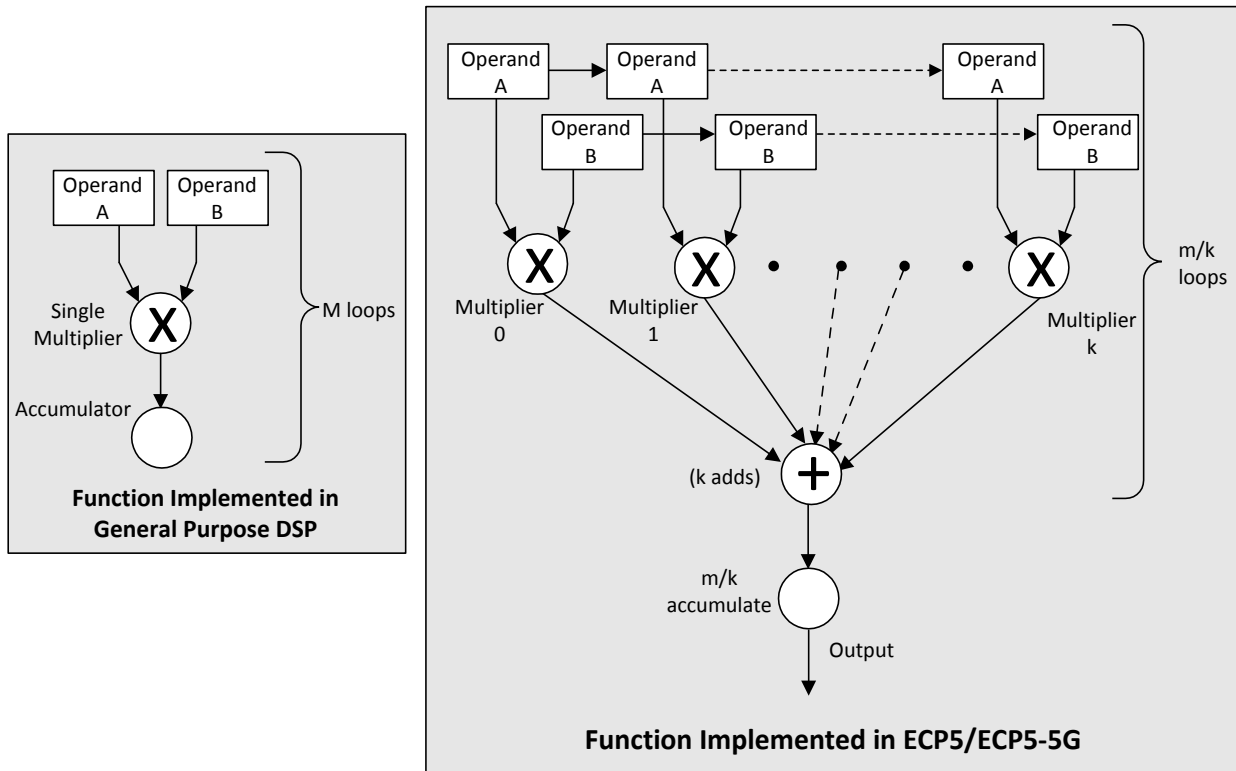


Figure 2.13. Comparison of General DSP and ECP5/ECP5-5G Approaches

2.9.2. sysDSP Slice Architecture Features

The ECP5/ECP5-5G sysDSP Slice has been significantly enhanced to provide functions needed for advanced processing applications. These enhancements provide improved flexibility and resource utilization.

The ECP5/ECP5-5G sysDSP Slice supports many functions that include the following:

- Symmetry support. The primary target application is wireless. 1D Symmetry is useful for many applications that use FIR filters when their coefficients have symmetry or asymmetry characteristics. The main motivation for using 1D symmetry is cost/size optimization. The expected size reduction is up to 2x.
 - Odd mode – Filter with Odd number of taps
 - Even mode – Filter with Even number of taps
 - Two dimensional (2D) symmetry mode – supports 2D filters for mainly video applications
- Dual-multiplier architecture. Lower accumulator overhead to half and the latency to half compared to single multiplier architecture
- Fully cascable DSP across slices. Support for symmetric, asymmetric and non-symmetric filters.
- Multiply (one 18x36, two 18x18 or four 9x9 Multiplies per Slice)
- Multiply (36x36 by cascading across two sysDSP slices)
- Multiply Accumulate (supports one 18x36 multiplier result accumulation or two 18x18 multiplier result accumulation)
- Two Multiplies feeding one Accumulate per cycle for increased processing with lower latency (two 18x18 Multiplies feed into an accumulator that can accumulate up to 52 bits)
- Pipeline registers
- 1D Symmetry support. The coefficients of FIR filters have symmetry or negative symmetry characteristics.
 - Odd mode – Filter with Odd number of taps
 - Even mode – Filter with Even number of taps
- 2D Symmetry support. The coefficients of 2D FIR filters have symmetry or negative symmetry characteristics.
 - 3*3 and 3*5 – Internal DSP Slice support

2.14.4. On-Chip Programmable Termination

The ECP5/ECP5-5G devices support a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 50 Ω , 75 Ω , or 150 Ω .
- Common mode termination of 100 Ω for differential inputs.

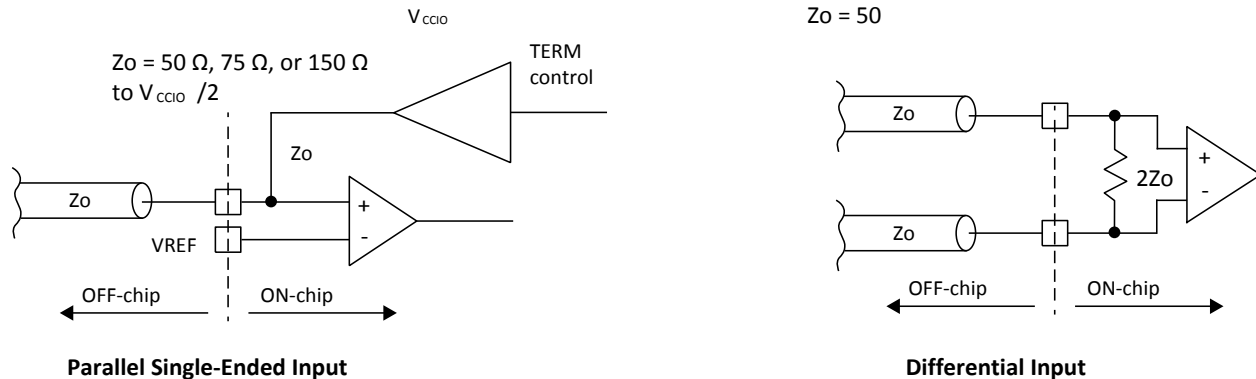


Figure 2.26. On-Chip Termination

See Table 2.12 for termination options for input modes.

Table 2.12. On-Chip Termination Options for Input Modes

IO_TYPE	Terminate to $V_{CCIO}/2^*$	Differential Termination Resistor*
LVDS25	—	100
BLVDS25	—	100
MLVDS	—	100
LVPECL33	—	100
subLVDS	—	100
SLVS	—	100
HSUL12	50, 75, 150	—
HSUL12D	—	100
SSTL135_I / II	50, 75, 150	—
SSTL135D_I / II	—	100
SSTL15_I / II	50, 75, 150	—
SSTL15D_I / II	—	100
SSTL18_I / II	50, 75, 150	—
SSTL18D_I / II	—	100

***Notes:**

TERMINATE to $V_{CCIO}/2$ (Single-Ended) and DIFFERENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.

Use of TERMINATE to $V_{CCIO}/2$ and DIFFERENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank. On-chip termination tolerance $\pm 20\%$.

Refer to [ECP5 and ECP5-5G sysIO Usage Guide \(TN1262\)](#) for on-chip termination usage and value ranges.

2.14.5. Hot Socketing

ECP5/ECP5-5G devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tristate until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. See the [Hot Socketing Specifications](#) section on page 48.

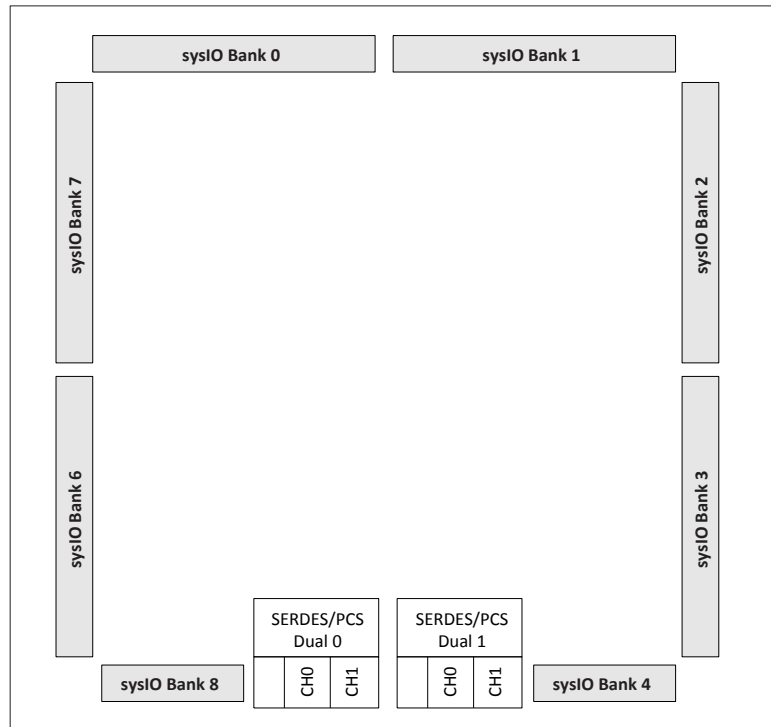


Figure 2.27. SERDES/PCS Duals (LFE5UM/LFE5UM5G-85)

Table 2.13. LFE5UM/LFE5UM5G SERDES Standard Support

Standard	Data Rate (Mb/s)	Number of General/Link Width	Encoding Style
PCI Express 1.1 and 2.0 2.02	2500	x1, x2, x4	8b10b
	5000 ²	x1, x2	8b10b
Gigabit Ethernet	1250	x1	8b10b
SGMII	1250	x1	8b10b
	2500	x1	8b10b
XAUI	3125	x4	8b10b
CPRI-1 CPRI-2 CPRI-3 CPRI-4 CPRI-5	614.4 1228.8 2457.6 3072.0 4915.2 ²	x1	8b10b
SD-SDI (259M, 344M) ¹	270	x1	NRZI/Scrambled
HD-SDI (292M)	1483.5	x1	NRZI/Scrambled
	1485	x1	NRZI/Scrambled
3G-SDI (424M)	2967 2970	x1	NRZI/Scrambled
	5000	—	—
JESD204A/B	3125	x1	8b/10b

Notes:

- For SD-SDI rate, the SERDES is bypassed and SERDES input signals are directly connected to the FPGA routing.
- For ECP5-5G family devices only.

Table 3.10. ECP5-5G

Symbol	Description	Typ	Max	Unit
Standby (Power Down)				
I _{CCA-SB}	V _{CCA} Power Supply Current (Per Channel)	4	9.5	mA
I _{CCHRX-SB} ⁴	V _{CCHRX} , Input Buffer Current (Per Channel)	—	0.1	mA
I _{CCHTX-SB}	V _{CCHTX} , Output Buffer Current (Per Channel)	—	0.9	mA
Operating (Data Rate = 5 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	58	67	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 3.2 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	48	57	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 2.5 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	44	53	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 1.25 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	36	46	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 270 Mb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	30	40	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	8	10	mA

Notes:

1. Rx Equalization enabled, Tx De-emphasis (pre-cursor and post-cursor) disabled
2. Per Channel current is calculated with both channels on in a Dual, and divide current by two. If only one channel is on, current will be higher.
3. To calculate with Tx De-emphasis enabled, use the Diamond Power Calculator tool.
4. For I_{CCHRX-SB}, during Standby, input termination on Rx are disabled.
5. For I_{CCHRX-OP}, during operational, the max specified when external AC coupling is used. If externally DC coupled, the power is based on current pulled down by external driver when the input is driven to LOW.

3.13. sysI/O Single-Ended DC Electrical Characteristics

Table 3.12. Single-Ended DC Characteristics

Input/Output Standard	V _{IL}		V _{IH}		V _{OL} Max (V)	V _{OH} Min (V)	I _{OL} ¹ (mA)	I _{OH} ¹ (mA)
	Min (V)	Max (V)	Min (V)	Max (V)				
LVC MOS33	−0.3	0.8	2.0	3.465	0.4	V _{CCIO} − 0.4	16, 12, 8, 4	−16, −12, −8, −4
LVC MOS25	−0.3	0.7	1.7	3.465	0.4	V _{CCIO} − 0.4	12, 8, 4	−12, −8, −4
LVC MOS18	−0.3	0.35 V _{CCIO}	0.65 V _{CCIO}	3.465	0.4	V _{CCIO} − 0.4	12, 8, 4	−12, −8, −4
LVC MOS15	−0.3	0.35 V _{CCIO}	0.65 V _{CCIO}	3.465	0.4	V _{CCIO} − 0.4	8, 4	−8, −4
LVC MOS12	−0.3	0.35 V _{CCIO}	0.65 V _{CCIO}	3.465	0.4	V _{CCIO} − 0.4	8, 4	−8, −4
LVTTL33	−0.3	0.8	2.0	3.465	0.4	V _{CCIO} − 0.4	16, 12, 8, 4	−16, −12, −8, −4
SSTL18_I (DDR2 Memory)	−0.3	V _{REF} − 0.125	V _{REF} + 0.125	3.465	0.4	V _{CCIO} − 0.4	6.7	−6.7
SSTL18_II	−0.3	V _{REF} −	V _{REF} + 0.125	3.465	0.28	V _{CCIO} − 0.28	13.4	−13.4
SSTL15_I (DDR3 Memory)	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	3.465	0.31	V _{CCIO} − 0.31	7.5	−7.5
SSTL15_II (DDR3 Memory)	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	3.465	0.31	V _{CCIO} − 0.31	8.8	−8.8
SSTL135_I (DDR3L Memory)	−0.3	V _{REF} − 0.09	V _{REF} + 0.09	3.465	0.27	V _{CCIO} − 0.27	7	−7
SSTL135_II (DDR3L Memory)	−0.3	V _{REF} − 0.09	V _{REF} + 0.09	3.465	0.27	V _{CCIO} − 0.27	8	−8
MIPI D-PHY (LP) ³	−0.3	0.55	0.88	3.465	—	—	—	—
HSUL12 (LPDDR2/3 Memory)	−0.3	V _{REF} − 0.1	V _{REF} + 0.1	3.465	0.3	V _{CCIO} − 0.3	4	−4

Notes:

1. For electromigration, the average DC current drawn by the I/O pads within a bank of I/Os shall not exceed 10 mA per I/O (All I/Os used in the same V_{CCIO}).
2. Not all IO types are supported in all banks. Refer to [ECP5 and ECP5-5G sysI/O Usage Guide \(TN1262\)](#) for details.
3. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVC MOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVC MOS12.

3.14.4. LVDS25E

The top and bottom sides of ECP5/ECP5-5G devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3.1 is one possible solution for point-to-point signals.

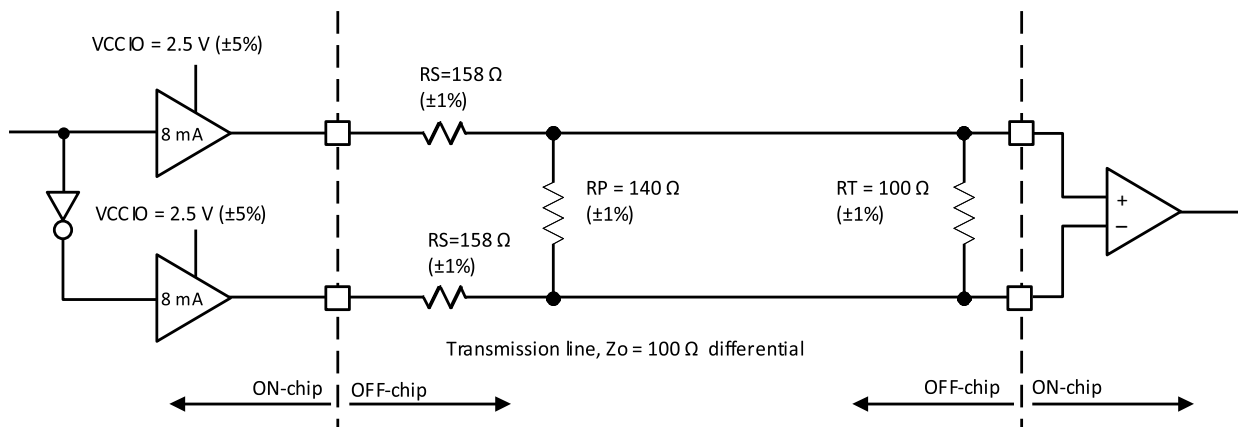


Figure 3.1. LVDS25E Output Termination Example

Table 3.14. LVDS25E DC Conditions

Parameter	Description	Typical	Unit
V _{CCIO}	Output Driver Supply (±5%)	2.50	V
Z _{OUT}	Driver Impedance	20	Ω
R _S	Driver Series Resistor (±1%)	158	Ω
R _P	Driver Parallel Resistor (±1%)	140	Ω
R _T	Receiver Termination (±1%)	100	Ω
V _{OH}	Output High Voltage	1.43	V
V _{OL}	Output Low Voltage	1.07	V
V _{OD}	Output Differential Voltage	0.35	V
V _{CM}	Output Common Mode Voltage	1.25	V
Z _{BACK}	Back Impedance	100.5	Ω
I _{DC}	DC Output Current	6.03	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

3.14.5. BLVDS25

The ECP5/ECP5-5G devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3.2 is one possible solution for bi-directional multi-point differential signals.

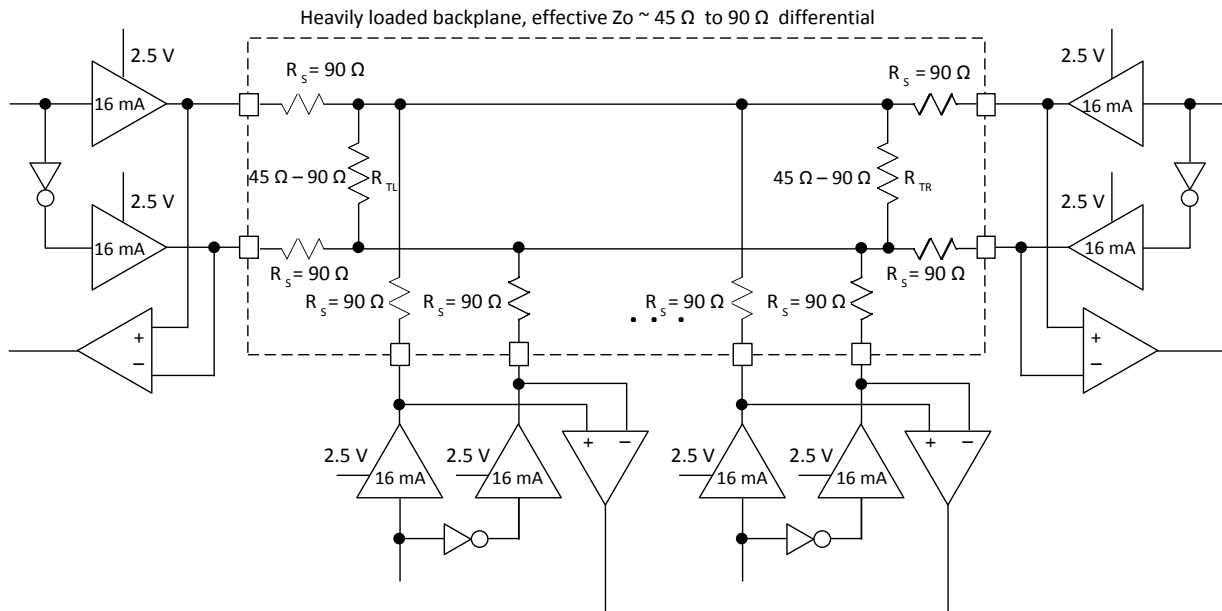


Figure 3.2. BLVDS25 Multi-point Output Example

Over recommended operating conditions.

Table 3.15. BLVDS25 DC Conditions

Parameter	Description	Typical		Unit
		Zo = 45 Ω	Zo = 90 Ω	
V _{CCIO}	Output Driver Supply (±5%)	2.50	2.50	V
Z _{OUT}	Driver Impedance	10.00	10.00	Ω
R _S	Driver Series Resistor (±1%)	90.00	90.00	Ω
R _{TL}	Driver Parallel Resistor (±1%)	45.00	90.00	Ω
R _{TR}	Receiver Termination (±1%)	45.00	90.00	Ω
V _{OH}	Output High Voltage	1.38	1.48	V
V _{OL}	Output Low Voltage	1.12	1.02	V
V _{OD}	Output Differential Voltage	0.25	0.46	V
V _{CM}	Output Common Mode Voltage	1.25	1.25	V
I _{DC}	DC Output Current	11.24	10.20	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

Parameter	Description	Device	-8		-7		-6		Unit
			Min	Max	Min	Max	Min	Max	
f _{DATA_DDR2} f _{DATA_DDR3} f _{DATA_DDR3L} f _{DATA_LPDDR2} f _{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f _{MAX_DDR2} f _{MAX_DDR3} f _{MAX_DDR3L} f _{MAX_LPDDR2} f _{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 WRITE (DQ Output Data are Centered to DQS)									
t _{DQVBS_DDR2} t _{DQVBS_DDR3} t _{DQVBS_DDR3L} t _{DQVBS_LPDDR2} t _{DQVBS_LPDDR3}	Data Output Valid before DQS Output	All Devices	—	–0.25	—	–0.25	—	–0.25	UI
t _{DQVAS_DDR2} t _{DQVAS_DDR3} t _{DQVAS_DDR3L} t _{DQVAS_LPDDR2} t _{DQVAS_LPDDR3}	Data Output Valid after DQS Output	All Devices	0.25	—	0.25	—	0.25	—	UI
f _{DATA_DDR2} f _{DATA_DDR3} f _{DATA_DDR3L} f _{DATA_LPDDR2} f _{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f _{MAX_DDR2} f _{MAX_DDR3} f _{MAX_DDR3L} f _{MAX_LPDDR2} f _{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz

Notes:

- Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond software.
- General I/O timing numbers are based on LVCMOS 2.5, 12 mA, Fast Slew Rate, 0pf load.
Generic DDR timing are numbers based on LVDS I/O.
DDR2 timing numbers are based on SSTL18.
DDR3 timing numbers are based on SSTL15.
LPDDR2 and LPDDR3 timing numbers are based on HSUL12.
- Uses LVDS I/O standard for measurements.
- Maximum clock frequencies are tested under best case conditions. System performance may vary upon the user environment.
- All numbers are generated with the Diamond software.

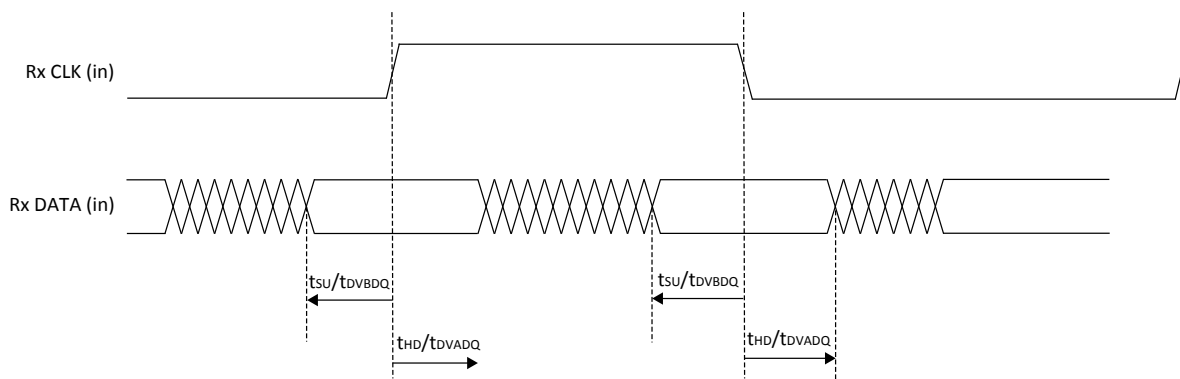


Figure 3.6. Receiver RX.CLK.Centered Waveforms

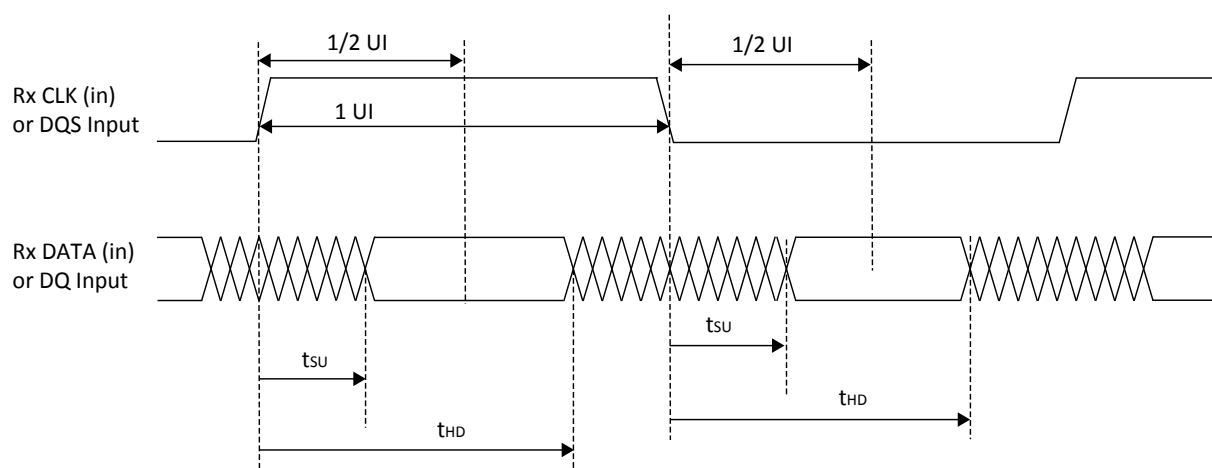


Figure 3.7. Receiver RX.CLK.Aligned and DDR Memory Input Waveforms

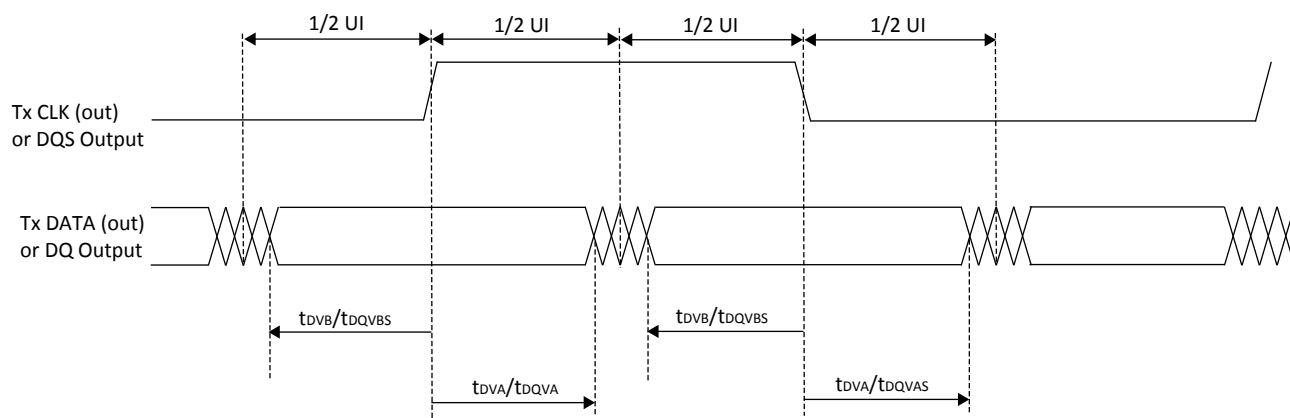


Figure 3.8. Transmit TX.CLK.Centered and DDR Memory Output Waveforms

3.27. XAUI/CPRI LV E.30 Electrical and Timing Characteristics

3.27.1. AC and DC Characteristics

Over recommended operating conditions.

Table 3.33. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T _{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance	—	80	100	120	Ω
J _{TX_DDJ} ^{2,3}	Output data deterministic jitter	—	—	—	0.17	UI
J _{TX_TJ} ^{1, 2, 3}	Total output data jitter	—	—	—	0.35	UI

Notes:

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Over recommended operating conditions.

Table 3.34. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z _{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J _{RX_DJ} ^{1, 2, 3}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
J _{RX_RJ} ^{1, 2, 3}	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
J _{RX_SJ} ^{1, 2, 3}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
J _{RX_TJ} ^{1, 2, 3}	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T _{RX_EYE}	Receiver eye opening	—	0.35	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

3.28. CPRI LV E.24/SGMII(2.5Gbps) Electrical and Timing Characteristics

3.28.1. AC and DC Characteristics

Table 3.35. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T _{RF} ¹	Differential rise/fall time	20% to 80%	—	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance	—	80	100	120	Ω
J _{TX_DDJ} ^{3,4}	Output data deterministic jitter	—	—	—	0.17	UI
J _{TX_TJ} ^{2, 3, 4}	Total output data jitter	—	—	—	0.35	UI

Notes:

1. Rise and Fall times measured with board trace, connector and approximately 2.5 pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Table 3.36. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z _{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J _{RX_DJ} ^{2, 3, 4}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
J _{RX_RJ} ^{2, 3, 4}	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
J _{RX_SJ} ^{2, 3, 4}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
J _{RX_TJ} ^{1, 2, 3, 4}	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T _{RX_EYE}	Receiver eye opening	—	0.35	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

3.29. Gigabit Ethernet/SGMII(1.25Gbps)/CPRI LV E.12 Electrical and Timing Characteristics

3.29.1. AC and DC Characteristics

Table 3.37. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T _{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance	—	80	100	120	Ω
J _{TX_DDJ} ^{2, 3}	Output data deterministic jitter	—	—	—	0.10	UI
J _{TX_TJ} ^{1, 2, 3}	Total output data jitter	—	—	—	0.24	UI

Notes:

1. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Table 3.38. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 1.25 GHz	10	—	—	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 1.25 GHz	6	—	—	dB
Z _{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J _{RX_DJ} ^{1, 2, 3, 4}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.34	UI
J _{RX_RJ} ^{1, 2, 3, 4}	Random jitter tolerance (peak-to-peak)	—	—	—	0.26	UI
J _{RX_SJ} ^{1, 2, 3, 4}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.11	UI
J _{RX_TJ} ^{1, 2, 3, 4}	Total jitter tolerance (peak-to-peak)	—	—	—	0.71	UI
T _{RX_EYE}	Receiver eye opening	—	0.29	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

3.30. SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

3.30.1. AC and DC Characteristics

Table 3.39. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
BR _{SDO}	Serial data rate	—	270	—	2975	Mb/s
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mb/s ⁶	—	—	0.2	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mb/s	—	—	0.2	UI
T _{JALIGNMENT} ^{1, 2}	Serial output jitter, alignment	2970 Mb/s	—	—	0.3	UI
T _{JTIMING}	Serial output jitter, timing	270 Mb/s ⁶	—	—	0.2	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mb/s	—	—	1	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mb/s	—	—	2	UI

Notes:

1. Timing jitter is measured in accordance with SMPTE serial data transmission standards.
2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
3. All Tx jitter are measured at the output of an industry standard cable driver, with the Lattice SERDES device configured to 50 Ω output impedance connecting to the external cable driver with differential signaling.
4. The cable driver drives: RL=75 Ω, AC-coupled at 270, 1485, or 2970 Mb/s.
5. All LFE5UM/LFE5UM5G devices are compliant with all SMPTE compliance tests, except 3G-SDI Level-A pathological compliance pattern test.
6. 270 Mb/s is supported with Rate Divider only.

Table 3.40. Receive

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
BR _{SDI}	Serial input data rate	—	270	—	2970	Mb/s

Table 3.41. Reference Clock

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
F _{VCLK}	Video output clock frequency	—	54	—	148.5	MHz
DC _v	Duty cycle, video clock	—	45	50	55	%

Note: SD-SDI (270 Mb/s) is supported with Rate Divider only. For Single Rate: Reference Clock = 54 MHz and Rate Divider = /2. For Tri-Rate: Reference Clock = 148.5 MHz and Rate Divider = /11.

3.31. sysCONFIG Port Timing Specifications

Over recommended operating conditions.

Table 3.42. ECP5/ECP5-5G sysCONFIG Port Timing Specifications

Symbol	Parameter		Min	Max	Unit
POR, Configuration Initialization, and Wakeup					
t_{ICFG}	Time from the Application of V_{CC} , V_{CCAUX} or V_{CCIO8} (whichever is the last) to the rising edge of INITN	—	—	33	ms
t_{VMC}	Time from t_{ICFG} to the valid Master CCLK	—	—	5	us
t_{CZ}	CCLK from Active to High-Z	—	—	300	ns
Master CCLK					
f_{MCLK}	Frequency	All selected frequencies	–20	20	%
$t_{MCLK-DC}$	Duty Cycle	All selected frequencies	40	60	%
All Configuration Modes					
t_{PRGM}	PROGRAMN LOW pulse accepted	—	110	—	ns
t_{PRGMRJ}	PROGRAMN LOW pulse rejected	—	—	50	ns
t_{INITL}	INITN LOW time	—	—	55	ns
t_{DPPINT}	PROGRAMN LOW to INITN LOW	—	—	70	ns
$t_{DPPDONE}$	PROGRAMN LOW to DONE LOW	—	—	80	ns
t_{IODISS}	PROGRAMN LOW to I/O Disabled	—	—	150	ns
Slave SPI					
f_{CCLK}	CCLK input clock frequency	—	—	60	MHz
t_{CCLKH}	CCLK input clock pulsewidth HIGH	—	6	—	ns
t_{CCLKL}	CCLK input clock pulsewidth LOW	—	6	—	ns
t_{STSU}	CCLK setup time	—	1	—	ns
t_{STH}	CCLK hold time	—	1	—	ns
t_{STCO}	CCLK falling edge to valid output	—	—	10	ns
t_{STOZ}	CCLK falling edge to valid disable	—	—	10	ns
t_{STOV}	CCLK falling edge to valid enable	—	—	10	ns
t_{SCS}	Chip Select HIGH time	—	25	—	ns
t_{SCSS}	Chip Select setup time	—	3	—	ns
t_{SCSH}	Chip Select hold time	—	3	—	ns
Master SPI					
f_{CCLK}	Max selected CCLK output frequency	—	—	62	MHz
t_{CCLKH}	CCLK output clock pulse width HIGH	—	3.5	—	ns
t_{CCLKL}	CCLK output clock pulse width LOW	—	3.5	—	ns
t_{STSU}	CCLK setup time	—	5	—	ns
t_{STH}	CCLK hold time	—	1	—	ns
t_{CSSPI}	INITN HIGH to Chip Select LOW	—	100	200	ns
t_{CFGX}	INITN HIGH to first CCLK edge	—	—	150	ns
Slave Serial					
f_{CCLK}	CCLK input clock frequency	—	—	66	MHz
t_{SSCH}	CCLK input clock pulse width HIGH	—	5	—	ns
t_{SSCL}	CCLK input clock pulse width LOW	—	5	—	ns
t_{SUSCDI}	CCLK setup time	—	0.5	—	ns
$t_{HS CDI}$	CCLK hold time	—	1.5	—	ns

4. Pinout Information

4.1. Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[L/R] [Group Number]_[A/B/C/D]	I/O	<p>[L/R] indicates the L (Left), or R (Right) edge of the device. [Group Number] indicates the PIO [A/B/C/D] group.</p> <p>[A/B/C/D] indicates the PIO within the PIC to which the pad is connected.</p> <p>Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tristated with an internal pull-down resistor enabled. If any pin is not used (or not bonded to a package pin), it is tristated and default to have pull-down enabled after configuration.</p> <p>PIO A and B are grouped as a pair, and PIO C and D are group as a pair. Each pair supports true LVDS differential input buffer. Only PIO A and B pair supports true LVDS differential output buffer.</p> <p>Each A/B and C/D pair supports programmable on/off differential input termination of 100 Ω.</p>
P[T/B][Group Number]_[A/B]	I/O	<p>[T/B] indicates the T (top) or B (bottom) edge of the device. [Group Number] indicates the PIO [A/B] group.</p> <p>[A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with sysConfig pins. These pins, when not used as configuration pins, can be programmed as I/Os for user logic. During configuration, the pins not used in configuration are tristated with an internal pull-down resistor enabled. If any pin is not used (or not bonded to a package pin), it is tristated and default to have pull-down enabled after configuration.</p> <p>PIOs on top and bottom do not support differential input signaling or true LVDS output signaling, but it can support emulated differential output buffer.</p> <p>PIO A/B forms a pair of emulated differential output buffer.</p>
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
RESERVED	—	This pin is reserved and should not be connected to anything on the board.
GND	—	Ground. Dedicated pins.
V _{CC}	—	Power supply pins for core logic. Dedicated pins. V _{CC} = 1.1 V (ECP5), 1.2 V (ECP5UM5G)
V _{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers. V _{CCAUX} = 2.5 V.
V _{CCIOx}	—	Dedicated power supply pins for I/O bank x. V _{CCIO8} is used for configuration and JTAG.
VREF1_x	—	Reference supply pins for I/O bank x. Pre-determined shared pin in each bank are assigned as VREF1 input. When not used, they may be used as I/O pins.
PLL, DLL and Clock Functions		
[LOC]_[GPLL[T, C]]_IN	I	General Purpose PLL (GPLL) input pads: [LOC] = ULC, LLC, URC and LRC, T = true and C = complement. These pins are shared I/O pins. When not configured as GPLL input pads, they can be used as general purpose I/O pins.
GR_PCLK[Bank][num]	I	General Routing Signals in Banks 0, 1, 2, 3, 4, 6 and 7. There are two in each bank ([num] = 0, 1). Refer to ECP5 sysClock PLL/DLL Design and Usage Guide (TN1263) . These pins are shared I/O pins. When not configured as GR pins, they can be used as general purpose I/O pins.
PCLK[T/C][Bank]_[num]	I/O	General Purpose Primary CLK pads: [T/C] = True/Complement, [Bank] = (0, 1, 2, 3, 6 and 7). There are two in each bank ([num] = 0, 1). These are shared I/O pins. When not configured as PCLK pins, they can be used as general purpose I/O pins.